

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on) \max}$	$I_D$ $T_C = +25^\circ C$
-100V	240m $\Omega$ @ $V_{GS} = -10V$	-9A
	300m $\Omega$ @ $V_{GS} = -4.5V$	-8A

## Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

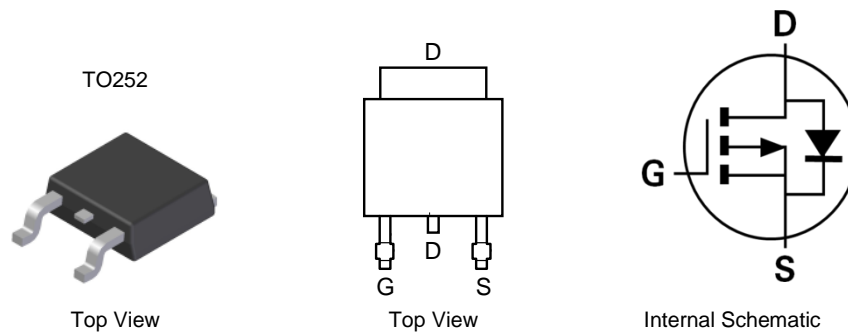
- DC-DC Converters
- Power Management Functions
- Analog Switch

## Features

- Low On-Resistance
- Low Input Capacitance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.33 grams (Approximate)

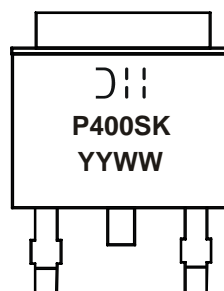


## Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP10H400SK3-13	Standard	TO252	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



⏏ = Manufacturer's Marking  
 P400SK = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 13 = 2013)  
 WW = Week (01 - 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	-100	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 5) V <sub>GS</sub> = -10V	Steady State	T <sub>C</sub> = +25°C	-9	A
		T <sub>C</sub> = +100°C	-5.5	
Maximum Body Diode Forward Current (Note 5)	I <sub>S</sub>	-4	A	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	-15	A	

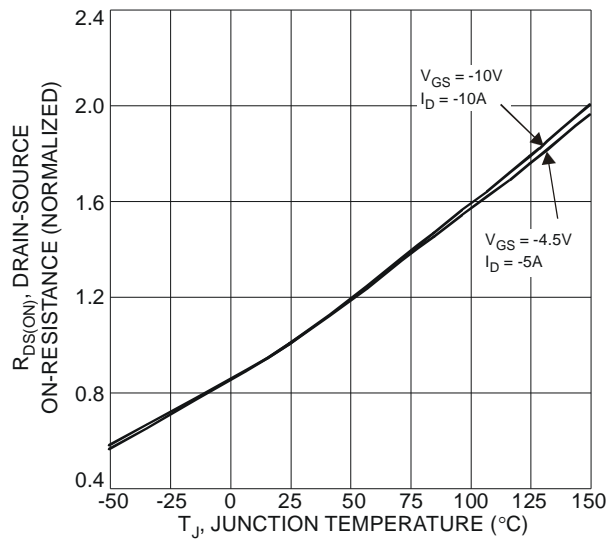
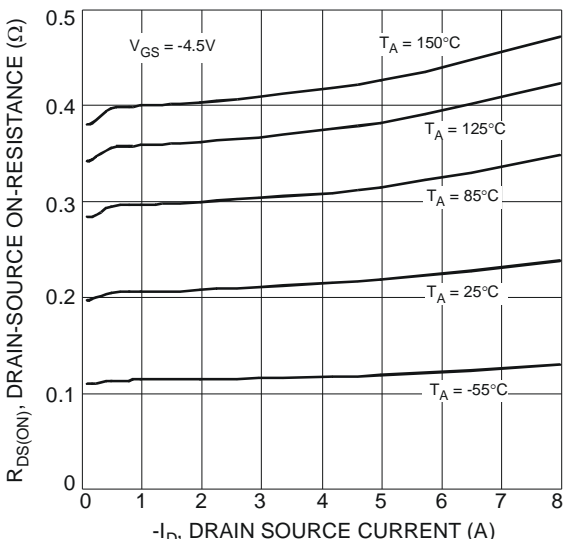
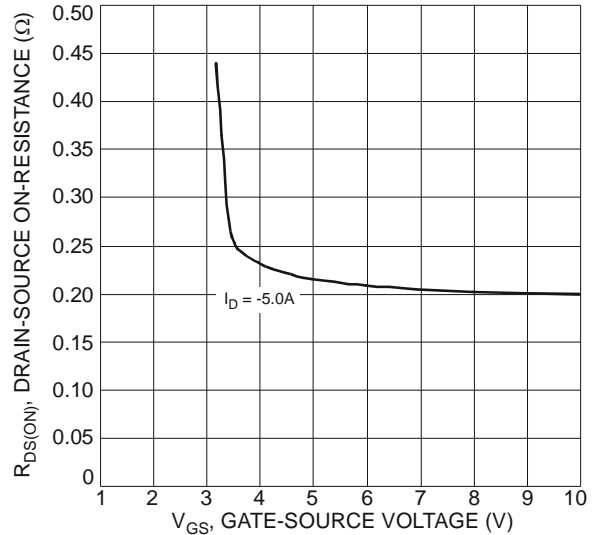
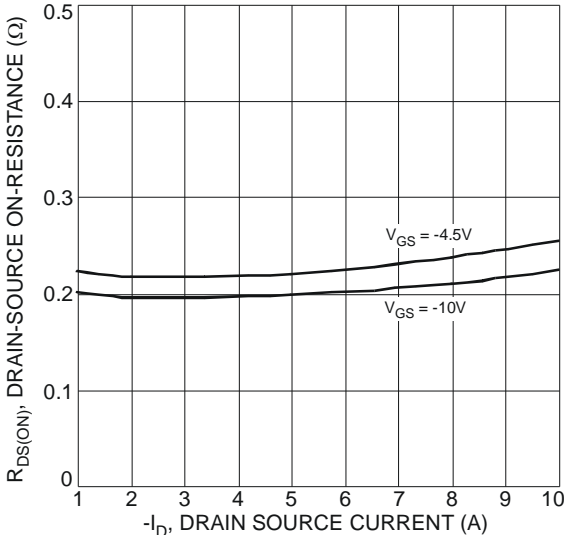
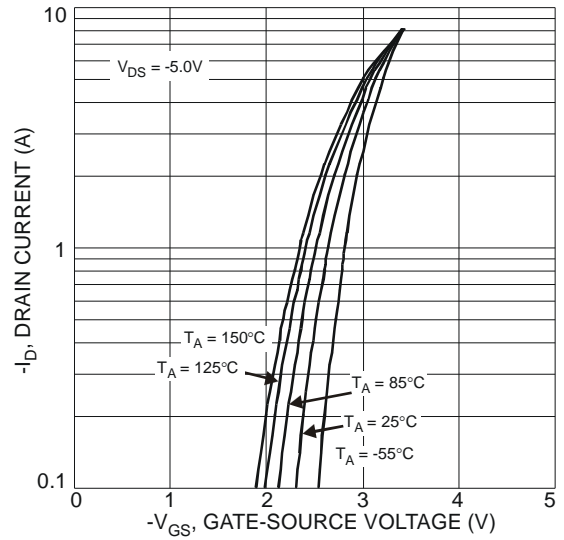
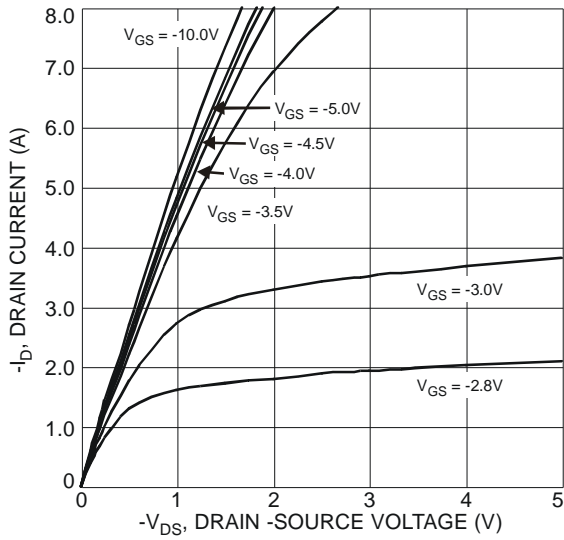
**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	P <sub>D</sub>	T <sub>C</sub> = +25°C	42	W
		T <sub>C</sub> = +100°C	17	
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	44	°C/W	
Thermal Resistance, Junction to Case (Note 5)	R <sub>θJC</sub>	3		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -80V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	—	-3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	190	240	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -5A
		—	210	300		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -5A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	1239	—	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	42	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	28	—		
Gate Resistance	R <sub>G</sub>	—	13	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	8.4	—	nC	V <sub>DS</sub> = -60V, I <sub>D</sub> = -5A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	17.5	—		
Gate-Source Charge	Q <sub>gs</sub>	—	2.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	3.2	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	9.1	—	ns	V <sub>DD</sub> = -50V, R <sub>G</sub> = 9.1Ω, I <sub>D</sub> = -5A
Turn-On Rise Time	t <sub>r</sub>	—	14.9	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	57.4	—		
Turn-Off Fall Time	t <sub>f</sub>	—	34.4	—		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	—	25.2	—	ns	V <sub>GS</sub> = 0V, I <sub>S</sub> = -5A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	—	24.5	—	nC	V <sub>GS</sub> = 0V, I <sub>S</sub> = -5A, di/dt = 100A/µs

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
  6. Short duration pulse test used to minimize self-heating effect.
  7. Guaranteed by design; not subject to production testing.



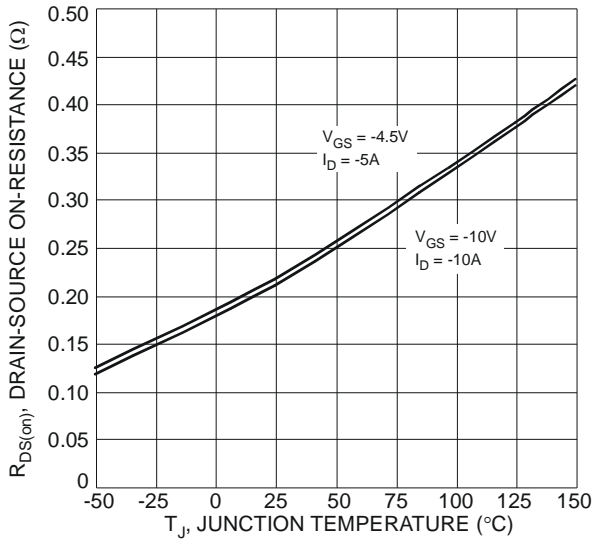


Fig. 7 On-Resistance Variation with Temperature

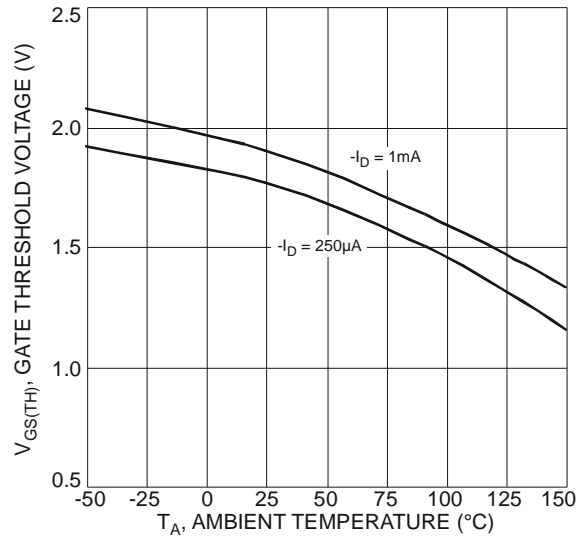


Fig. 8 Gate Threshold Variation vs. Ambient Temperature

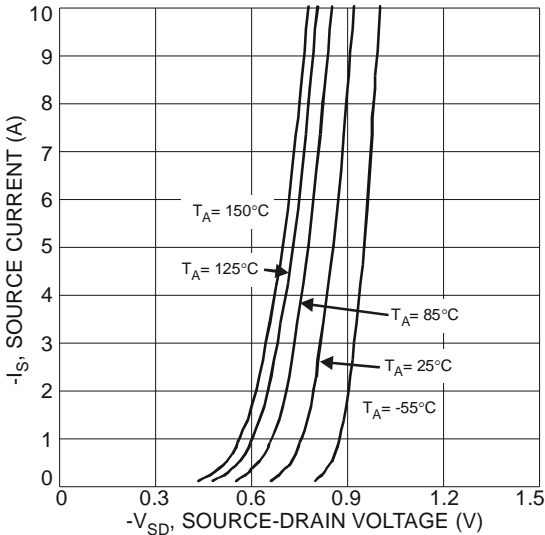


Fig. 9 Diode Forward Voltage vs. Current

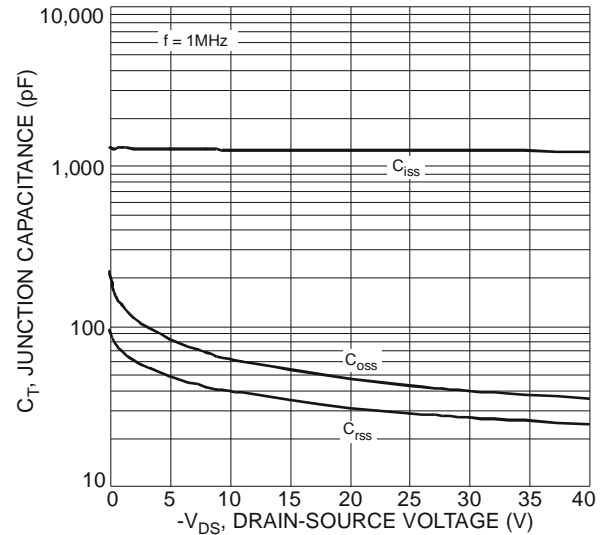


Fig. 10 Typical Junction Capacitance

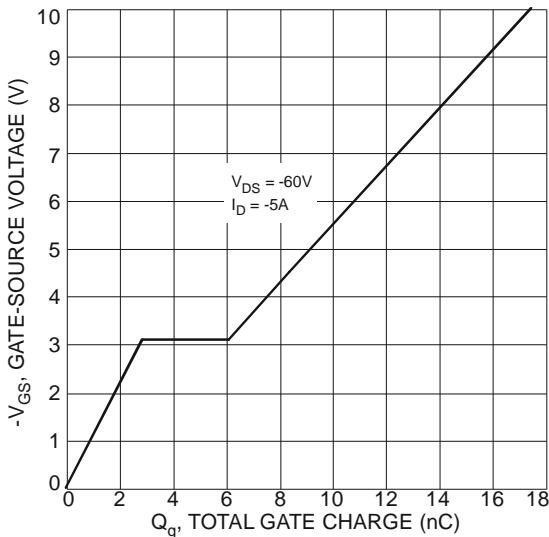
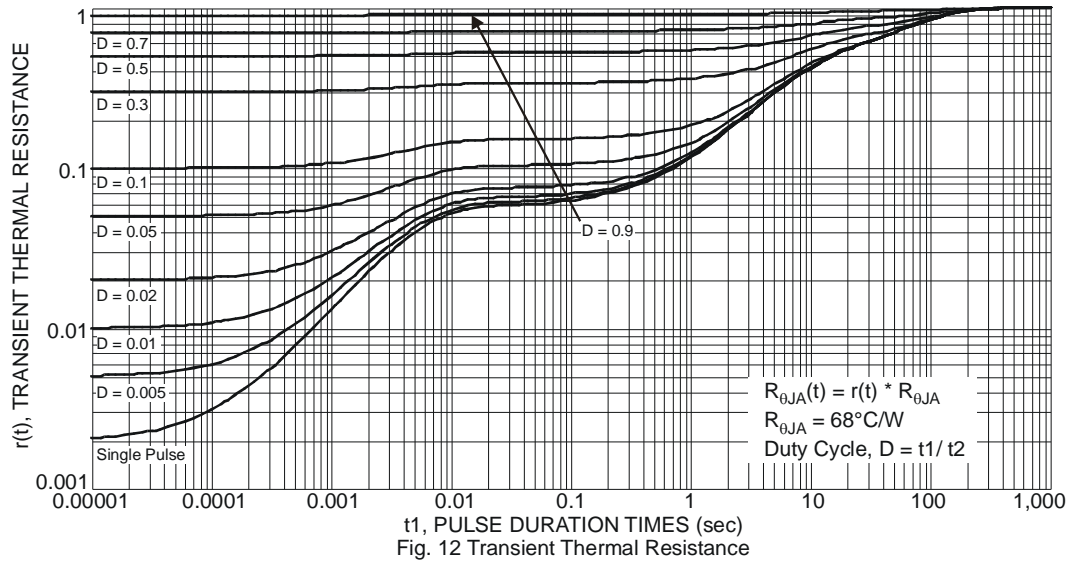
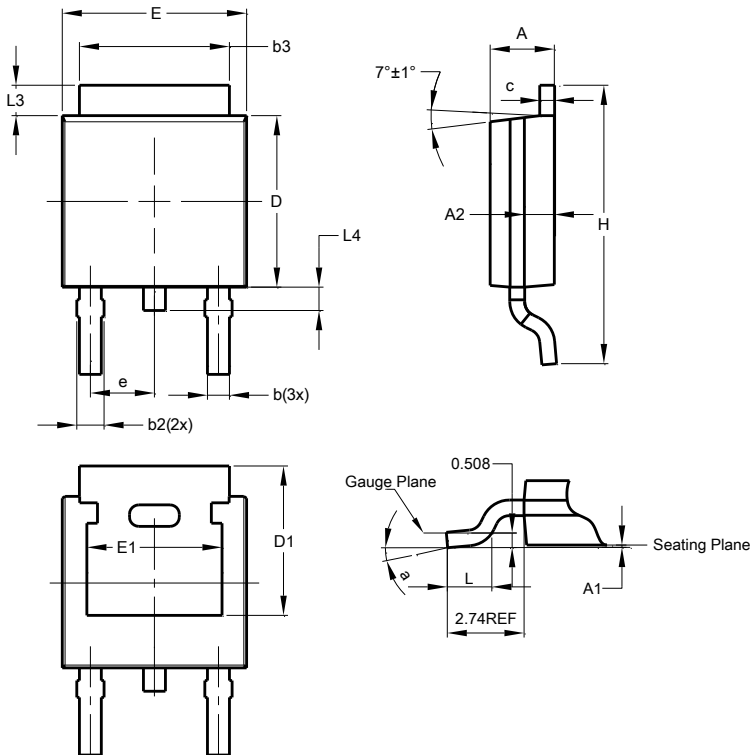


Fig. 11 Gate-Charge Characteristics



**Package Outline Dimensions**

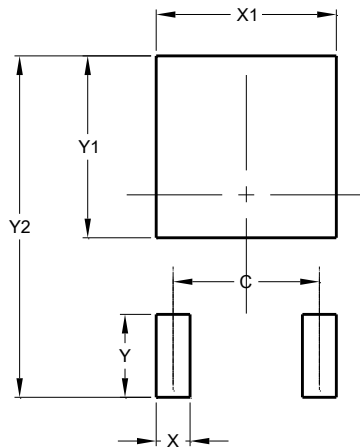
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
<b>All Dimensions in mm</b>			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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